

P-Channel 15-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)			
-15	0.0033 at $V_{GS} = -4.5 \text{ V}$	- 90	125 nC			
-10	0.0041 at $V_{GS} = -2.5 \text{ V}$	- 70	125110			

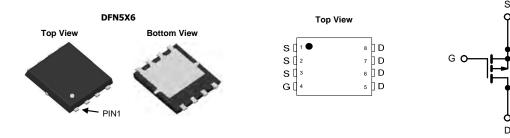
FEATURES

- · DT-Trench Power MOSFET
- 100 % R_q and UIS tested



APPLICATIONS

- Notebook
 - Load Switch



P-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 15	V		
Gate-Source Voltage		V_{GS}	± 8	¬	
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	I _D	- 90 ^a -70 ^a - 26 ^{b, c} - 19 ^{b, c}		
Pulsed Drain Current		I _{DM}	-180	Α	
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$	I _S	- 90 ^a - 46 ^{b, c}		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 40		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	100	mJ	
	T _C = 25 °C		105	W	
Maximum Power Dissipation	$T_C = 70 ^{\circ}C$	P _D	67.2		
	$T_A = 25 ^{\circ}C$	U	6.95 ^{b, c}		
	T _A = 70 °C		4.45 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature		260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R_{thJA}	18	25	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.1	1.5		

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. The DFN5x6 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 54 °C/W.

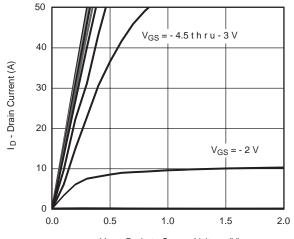


Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 15			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 31		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	i _D = - 250 μA		6.5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.3		- 1.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zara Cata Valtaga Drain Current	I _{DSS}	V _{DS} = -15 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C			- 10	- 10 µA	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 90			Α	
	<u> </u>	V _{GS} = - 4.5 V, I _D = - 20 A		0.0033	0.004		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 15 A		0.0041	0.005	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = -8 V, I _D = -20 A		96		S	
Dynamic ^b							
Input Capacitance	C _{iss}			27050			
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		3936		pF	
Reverse Transfer Capacitance	C _{rss}			1076			
Total Gate Charge	Qg	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 20 A		273	410	190	
				125	190		
Gate-Source Charge	Q_{gs}	V _{DS} = - 10 V, V _{GS} = - 2.5 V, I _D = - 15 A		39		nC	
Gate-Drain Charge	Q_{gd}			57			
Gate Resistance	R _g	f = 1 MHz		2.9		Ω	
Turn-On Delay Time	t _{d(on)}			29	30		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 15 Ω		16	30		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 10 A, V_{GEN} = - 2.5 V, R_g = 1 Ω		110	170	- ns	
Fall Time	t _f			30	50		
Turn-On Delay Time	t _{d(on)}			110	170		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 15 Ω		103	150		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 10 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		90	150		
Fall Time	t _f			50	75		
Drain-Source Body Diode Characteristi	cs						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			90	_	
Pulse Diode Forward Current ^a	I _{SM}				180	A	
Body Diode Voltage	V _{SD}	I _S = - 5 A		- 0.70	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			50	100	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = - 10 A, dl/dt = 100 A/μs, T _J = 25 °C		60	133	nC	
Reverse Recovery Fall Time	t _a			25			
Reverse Recovery Rise Time	t _b			24		ns	

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$ b. Guaranteed by design, not subject to production testing.

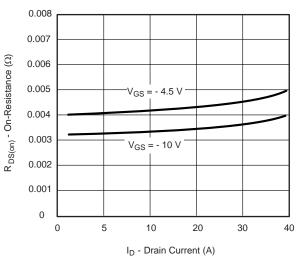
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



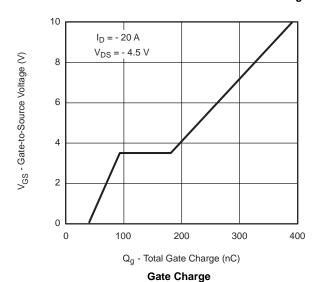


V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics

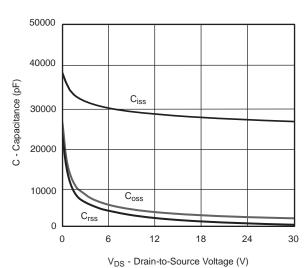


On-Resistance vs. Drain Current and Gate Voltage

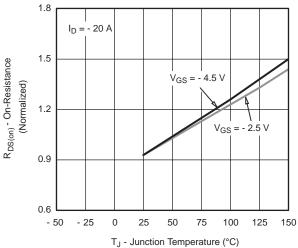


60 50 $T_C = -55$ °C I_D - Drain Current (A) 40 30 $T_C = 25$ °C 20 10 T_C = 125 °C 0.0 0.25 1.0 1.25 1.5

V_{DS} - Drain-to-Source Voltage (V) **Transfer Characteristics**

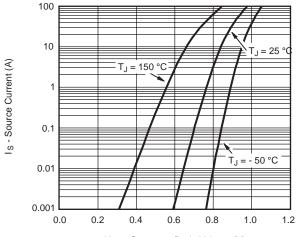


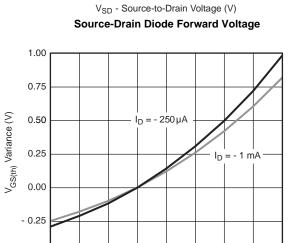




On-Resistance vs. Junction Temperature







T_J - Temperature (°C)

Threshold Voltage

50

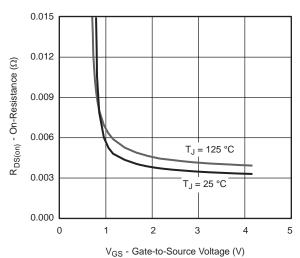
25

75

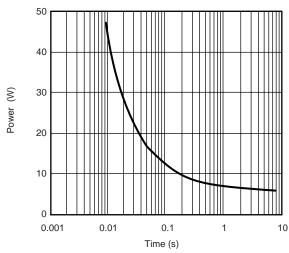
100

125

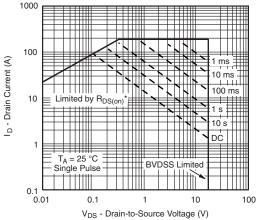
150



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



 * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

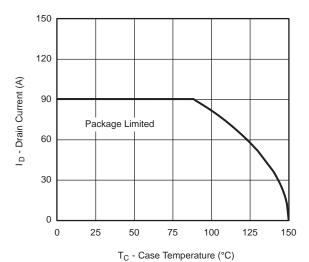
Safe Operating Area

- 0.50

- 50

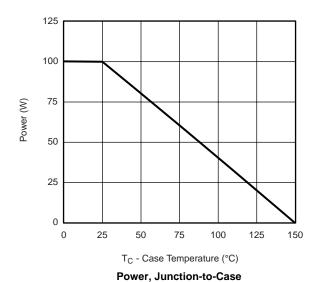
- 25

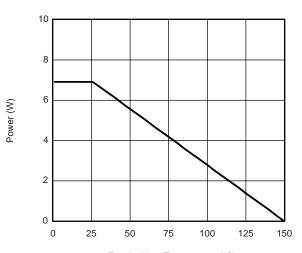




Comment Deneticent

Current Derating*



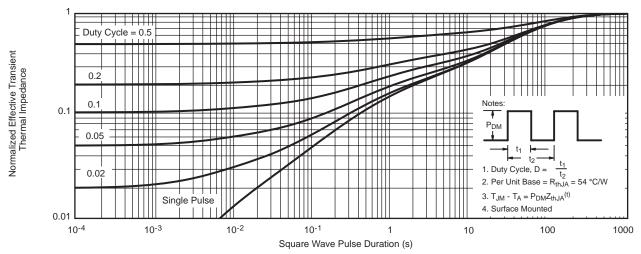


T_A - Ambient Temperature (°C)

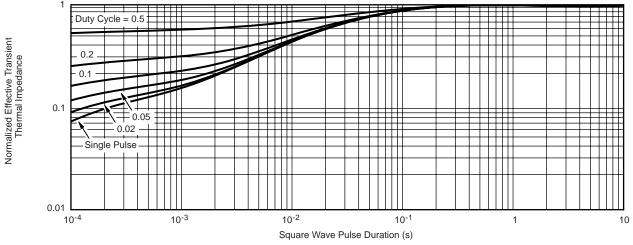
Power, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





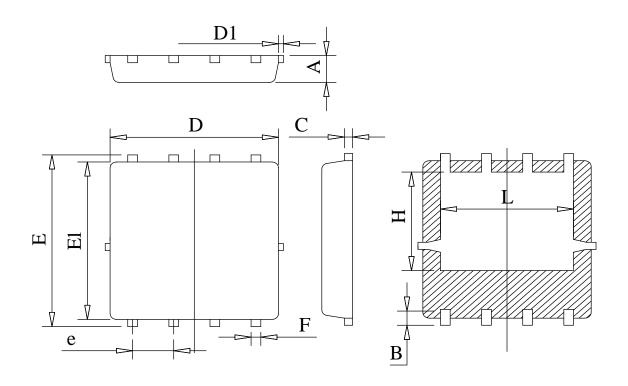
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25





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